

Silicon PNP Power Transistors

2N6034 2N6035 2N6036

DESCRIPTION

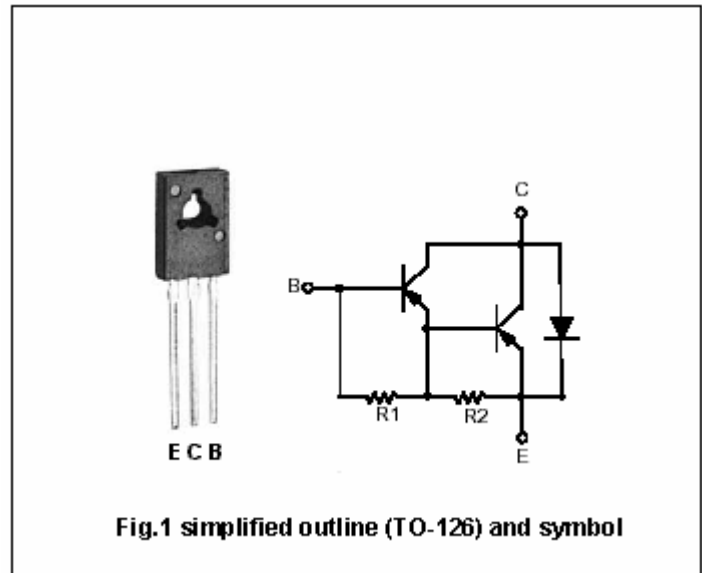
- With TO-126 package
- Complement to type 2N6037/6038/6039
- DARLINGTON
- High DC current gain

APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6034	-40	V
		2N6035	-60	
		2N6036	-80	
V _{CEO}	Collector-emitter voltage	2N6034	-40	V
		2N6035	-60	
		2N6036	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-4	A
I _{CM}	Collector current-peak		-8	A
I _B	Base current		-0.1	A
P _D	Total Power Dissipation	T _C =25□	40	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	3.12	□/W

Silicon PNP Power Transistors

2N6034 2N6035 2N6036

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N6034	-40			V
		2N6035	-60			
		2N6036	-80			
		I _C =-0.1A; I _B =0				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-2A; I _B =-8mA			-2.0	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-4A; I _B =-40mA			-3.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-4A; I _B =-40mA			-4.0	V
V _{BE}	Base-emitter on voltage	I _C =-2A; V _{CE} =-3V			-2.8	V
I _{CEO}	Collector cut-off current	V _{CE} =Rated V _{CE0} ; I _B =0			-0.1	mA
I _{CEx}	Collector cut-off current	V _{CE} =Rated V _{CE0} ; V _{BE(off)} =1.5V T _C =125°C			-0.1 -0.5	mA
I _{CBO}	Collector cut-off current	V _{CB} =Rated V _{CBO} ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-2.0	mA
h _{FE-1}	DC current gain	I _C =-0.5A; V _{CE} =-3V	500			
h _{FE-2}	DC current gain	I _C =-2A; V _{CE} =-3V	750		15000	
h _{FE-3}	DC current gain	I _C =-4A; V _{CE} =-3V	100			
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=0.1MHz			200	pF

Silicon PNP Power Transistors

2N6034 2N6035 2N6036

PACKAGE OUTLINE

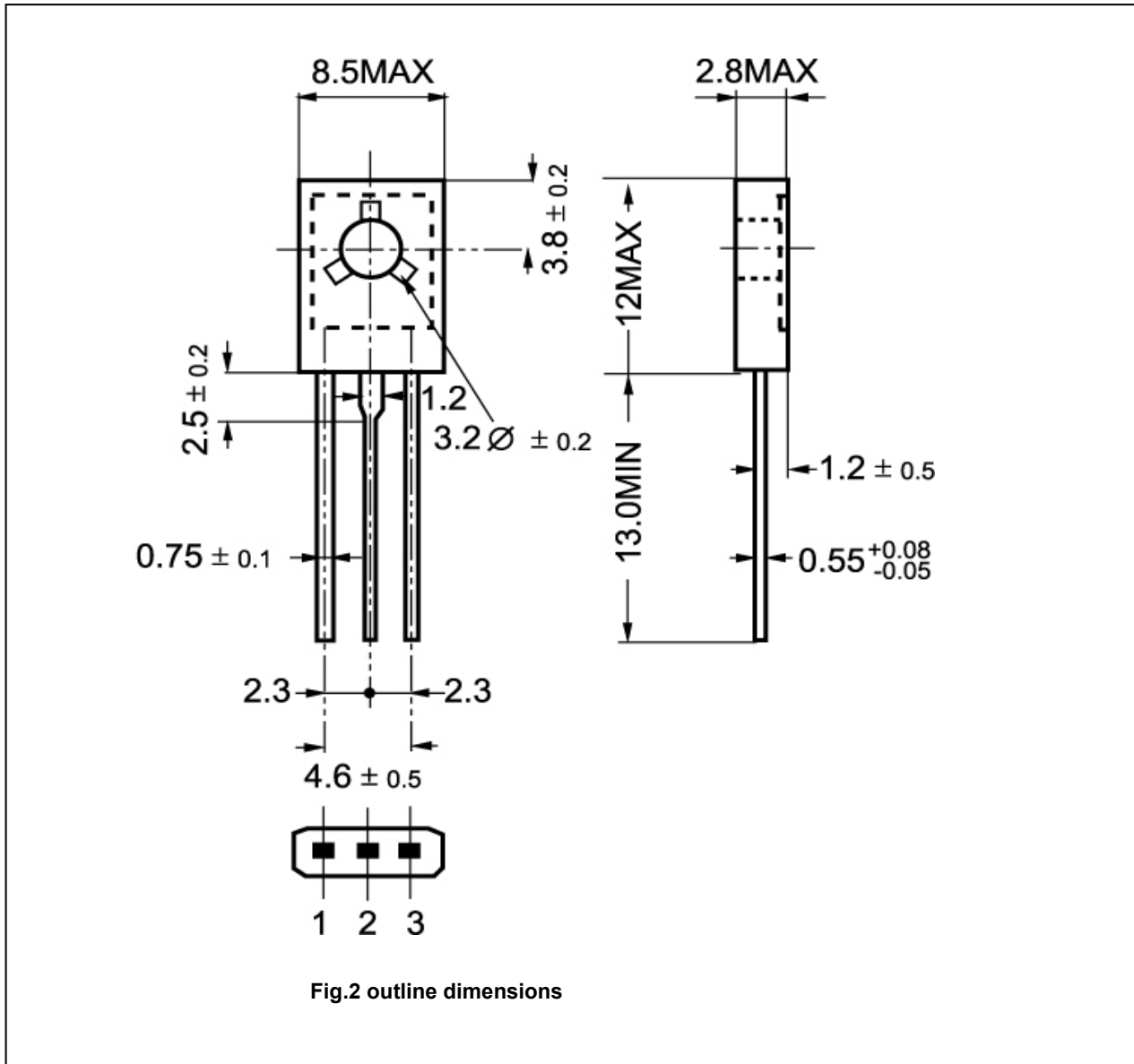


Fig.2 outline dimensions